

1. Scope :

This specification applies to P/N silicon zener diode chips,
Device NO. SD-30814G

2. Structure :

- 2-1. Planar type : P/N Diode
- 2-2. Electrodes :
 - Top side : Gold Pad.
 - Back side : Gold Layer.

3. Size :

- 3-1. Chip size : $195 \pm 20 \mu\text{m} \times 195 \pm 20 \mu\text{m}$ ($7.8 \pm 0.8 \text{ mils} \times 7.8 \pm 0.8 \text{ mils}$).
- 3-2. Chip thickness : $100 \pm 20 \mu\text{m}$ ($3.9 \pm 0.8 \text{ mils}$).
- 3-3. Bonding pad : $150 \mu\text{m} \times 150 \mu\text{m}$ ($5.9 \text{ mils} \times 5.9 \text{ mils}$).
- 3-4. Pattern drawing : Refer to the attached drawing.
- 3-5. Fiducial mark does not apply any characteristics or any incoming inspection.

4. Electrical characteristics ($T_a = 25 \text{ }^\circ\text{C}$)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse Leakage Current	I_R	$V_R=12\text{V}$ $E_e=0\text{mW/cm}^2$			500	nA
Zener Voltage	V_Z	$I_z=5\text{mA}$ $E_e=0\text{mW/cm}^2$	12		16	V
Forward Voltage	V_F	$I_F=20\text{mA}$ $E_e=0\text{mW/cm}^2$			1200	mV

